

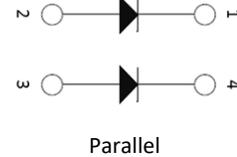
| | |
|-------------|--------|
| VDC | 1200 V |
| I_F | 60 A |
| $T_{j,max}$ | 175 °C |

1200V SiC Power Module Dual Diode Pack

Features

- SiC Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on V_F
- Low stray inductance
- High junction temperature operation

Package



Benefits

- Outstanding performance at high frequency operation
- Low loss and low EMI noise
- Very rugged and easy mount
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_F
- RoHS compliant

| Part # | Package | Marking |
|-----------------|---------|-----------------|
| GHXS060B120S-D3 | SOT-227 | GHXS060B120S-D3 |

Applications

- DC power supply
- Induction heater
- Welding equipment
- Charging station



Maximum Ratings, at $T_j=25\text{ °C}$, unless otherwise specified (per leg)

| Characteristics | Symbol | Conditions | Value | Unit |
|--|---------------|---|-----------|------------------|
| Continuous forward current | I_F | $T_C=25\text{ °C}$, $T_j=175\text{ °C}$ | 114 | A |
| | | $T_C=125\text{ °C}$, $T_j=175\text{ °C}$ | 60 | |
| | | $T_C=150\text{ °C}$, $T_j=175\text{ °C}$ | 38 | |
| Surge non-repetitive forward current sine halfwave | I_{FSM} | $T_C=25\text{ °C}$, $T_j=25\text{ °C}$, $t_p=8.3\text{ ms}$ | 500 | A |
| | | $T_C=110\text{ °C}$, $T_j=110\text{ °C}$, $t_p=8.3\text{ ms}$ | 430 | |
| Non-repetitive peak forward current | $I_{F,max}$ | $T_C=25\text{ °C}$, $t_p=10\text{ }\mu\text{s}$ | 1200 | A |
| i^2t value | $\int i^2 dt$ | $T_C=25\text{ °C}$, $t_p=8.3\text{ ms}$ | 1038 | A ² s |
| | | $T_C=110\text{ °C}$, $t_p=8.3\text{ ms}$ | 767 | |
| Repetitive peak reverse voltage | V_{RRM} | $T_j \geq 25\text{ °C}$ | 1200 | V |
| Diode dv/dt ruggedness | dv/dt | Turn-on slew rate, repetitive | 200 | V/ns |
| Power dissipation | P_{tot} | $T_C=25\text{ °C}$ | 375 | W |
| Operating junction temperature | T_j | | -55...175 | °C |
| Storage temperature | $T_{storage}$ | | -55...150 | °C |

Electrical Characteristics, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified (per leg)

| Characteristics | Symbol | Conditions | Values | | | Unit |
|-------------------------|----------|---|--------|------|------|---------------|
| | | | min. | typ. | max. | |
| DC blocking voltage | V_{DC} | $I_R=120\mu\text{A}$, $T_j=25\text{ }^\circ\text{C}$ | 1200 | - | - | V |
| Diode forward voltage | V_F | $I_F=60\text{A}$, $T_j=25\text{ }^\circ\text{C}$ | - | 1.50 | 1.65 | V |
| | | $I_F=60\text{A}$, $T_j=125\text{ }^\circ\text{C}$ | - | 1.83 | - | |
| | | $I_F=60\text{A}$, $T_j=175\text{ }^\circ\text{C}$ | - | 2.12 | 2.70 | |
| Reverse current | I_R | $V_R=1200\text{V}$, $T_j=25\text{ }^\circ\text{C}$ | - | 4 | 120 | μA |
| | | $V_R=1200\text{V}$, $T_j=125\text{ }^\circ\text{C}$ | - | 42 | - | |
| | | $V_R=1200\text{V}$, $T_j=175\text{ }^\circ\text{C}$ | - | 185 | 1800 | |
| Total capacitive charge | Q_C | $V_R=800\text{V}$, $T_j=25\text{ }^\circ\text{C}$ | - | 343 | - | nC |
| Total capacitance | C | $V_R=1\text{V}$, $f=1\text{ MHz}$ | - | 3828 | - | pF |
| | | $V_R=400\text{V}$, $f=1\text{ MHz}$ | - | 323 | - | |
| | | $V_R=800\text{V}$, $f=1\text{ MHz}$ | - | 235 | - | |

Thermal and Package Characteristics, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified

| Characteristics | Symbol | Conditions | Values | | | Unit |
|-----------------------------------|------------|---|--------|------|------|--------------------|
| | | | min. | typ. | max. | |
| Thermal resistance, junction-case | R_{thJC} | Per leg | - | 0.27 | 0.40 | $^\circ\text{C/W}$ |
| Mounting torque | M_d | M4-0.7 screws | 1.1 | - | 1.5 | N-m |
| Terminal connection torque | M_{dt} | M4-0.7 screws | - | 1.1 | 1.3 | N-m |
| Package weight | W_t | | - | 32 | - | g |
| Isolation voltage | V_{ISOL} | $I_{ISOL} < 1\text{ mA}$, 50/60 Hz, 1 min | 2500 | - | - | V |

Typical Performance Per Leg

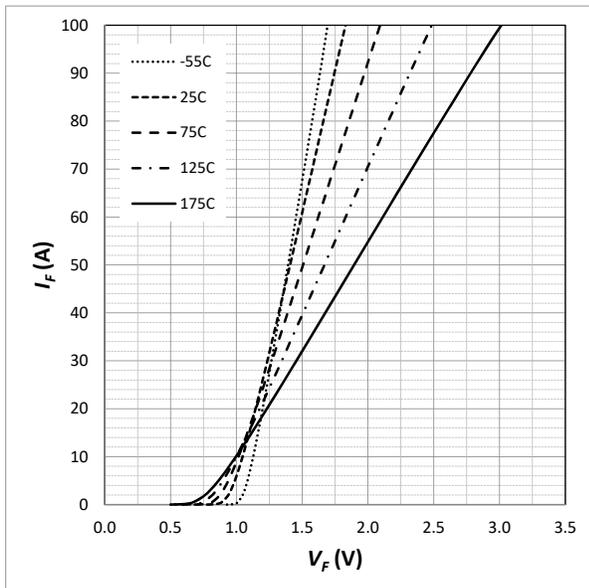


Fig. 1 Forward Characteristics (parameterized on T_j)

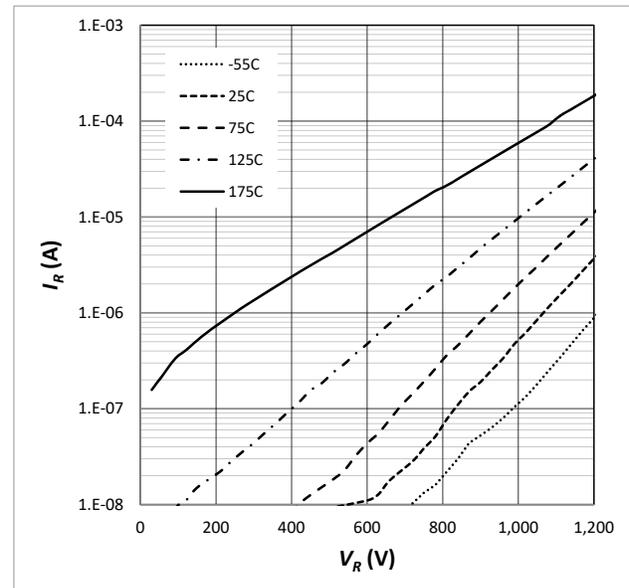


Fig. 2 Reverse Characteristics (parameterized on T_j)

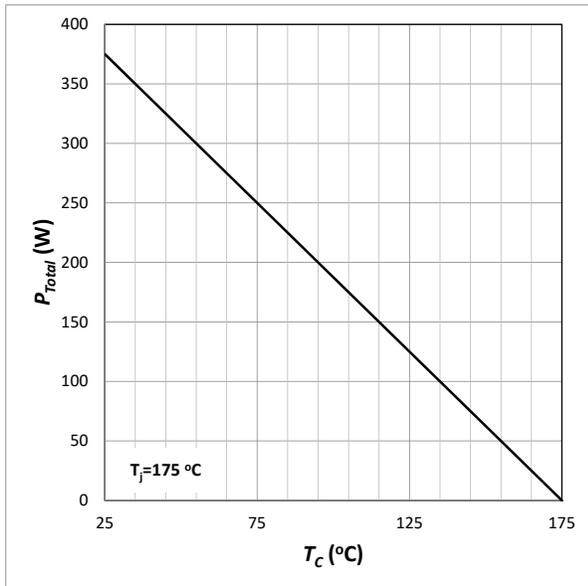


Fig. 3 Power Derating

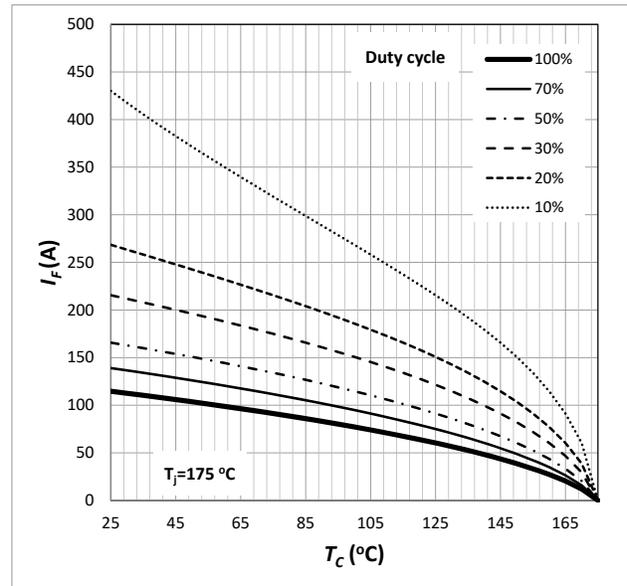


Fig. 4 Current Derating

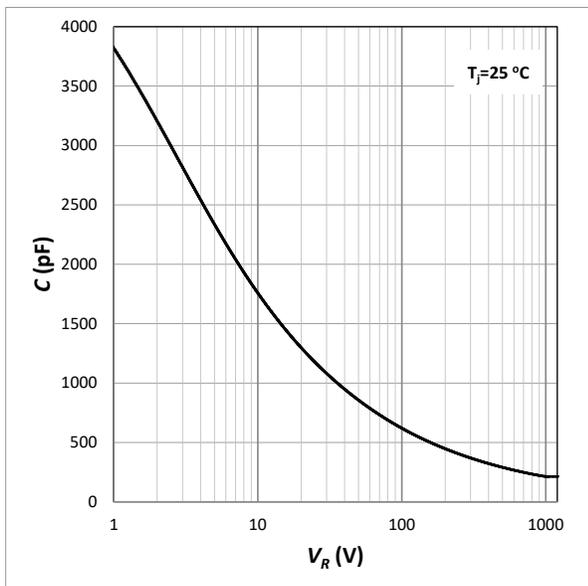


Fig. 5 Capacitance

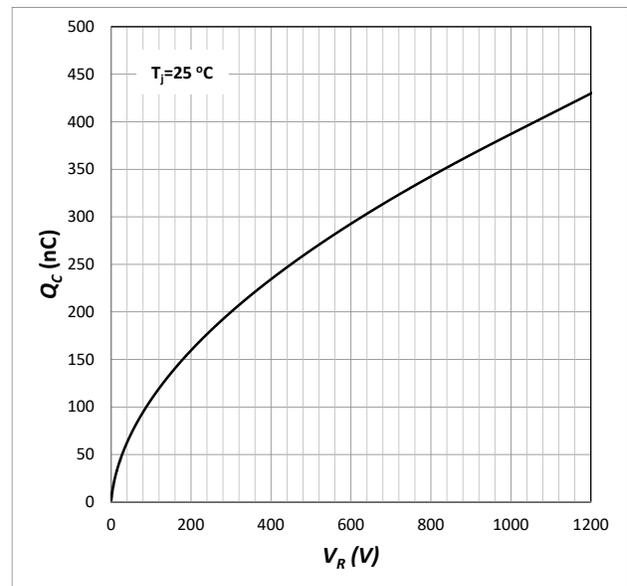


Fig. 6 Capacitive Charge

1200V SiC Power Module

GHXS060B120S-D3

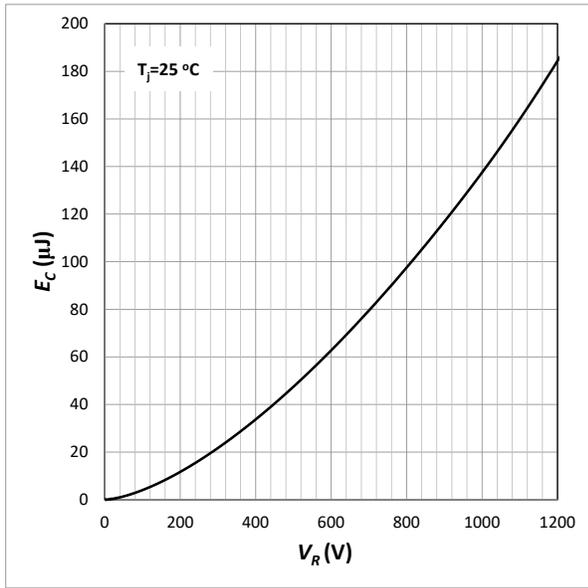


Fig. 7 Typical Capacitance Stored Energy

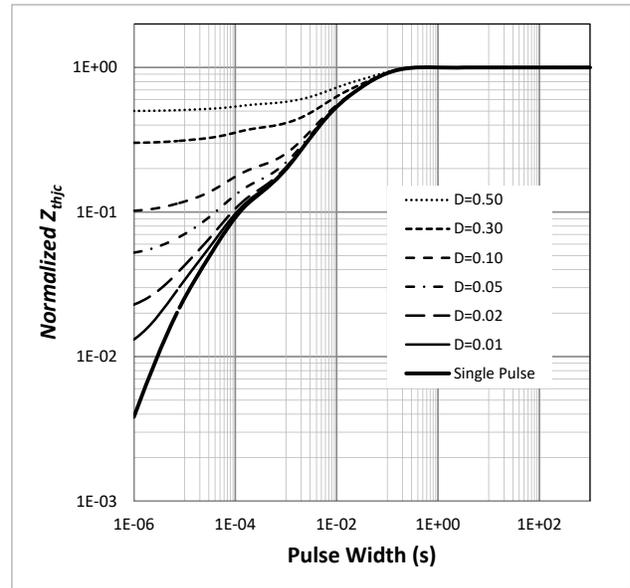
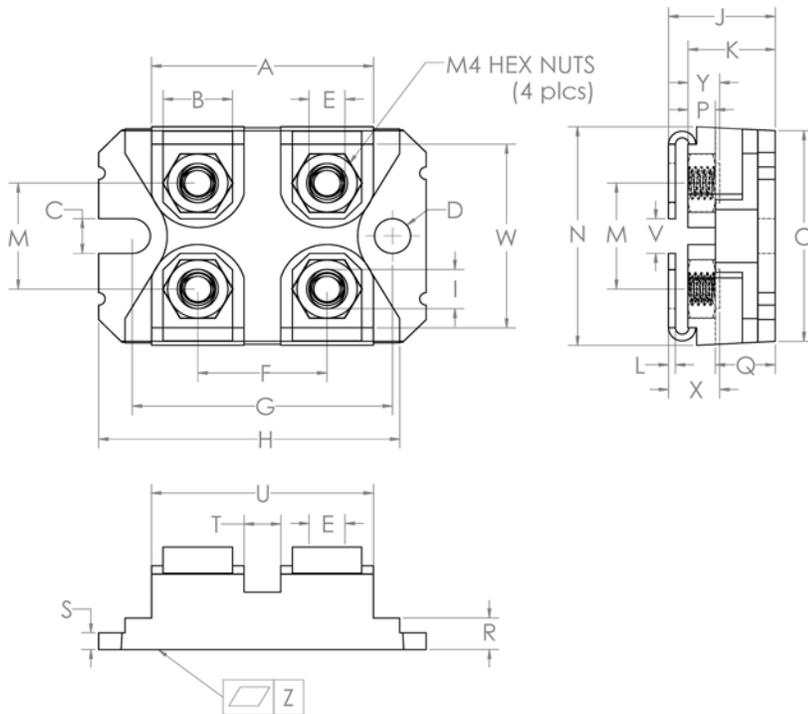


Fig. 8 Transient Thermal Impedance

Package Dimensions SOT-227



| Sym | Millimeters | | Inches | |
|-----|-------------|-------|--------|-------|
| | Min | Max | Min | Max |
| A | 31.67 | 31.90 | 1.247 | 1.256 |
| B | 7.95 | 8.18 | 0.313 | 0.322 |
| C | 4.14 | 4.24 | 0.163 | 0.167 |
| D | 4.14 | 4.24 | 0.163 | 0.167 |
| E | 4.14 | 4.24 | 0.163 | 0.167 |
| F | 14.94 | 15.09 | 0.588 | 0.594 |
| G | 30.15 | 30.25 | 1.187 | 1.191 |
| H | 38.00 | 38.10 | 1.496 | 1.500 |
| I | 4.75 | 4.83 | 0.187 | 0.190 |
| J | 11.68 | 12.19 | 0.460 | 0.480 |
| K | 9.45 | 9.60 | 0.372 | 0.378 |
| L | 0.76 | 0.84 | 0.030 | 0.033 |
| M | 12.62 | 12.88 | 0.497 | 0.507 |
| N | 25.15 | 25.30 | 0.990 | 0.996 |
| O | 24.79 | 25.04 | 0.976 | 0.986 |
| P | 3.02 | 3.15 | 0.119 | 0.124 |
| Q | 6.71 | 6.96 | 0.264 | 0.274 |
| R | 4.17 | 4.42 | 0.164 | 0.174 |
| S | 2.08 | 2.13 | 0.082 | 0.084 |
| T | 3.28 | 3.63 | 0.129 | 0.143 |
| U | 26.75 | 26.90 | 1.053 | 1.059 |
| V | 3.86 | 4.24 | 0.152 | 0.167 |
| W | 20.55 | 26.90 | 0.809 | 0.814 |
| X | 5.45 | 5.85 | 0.215 | 0.230 |
| Y | 3.15 | 3.66 | 0.124 | 0.144 |
| Z | 0.00 | 0.13 | 0.000 | 0.005 |